

N-Channel 22-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^d
24°C	0.006 @ $V_{GS} = 10$ V	80
	0.0095 @ $V_{GS} = 4.5$ V	64

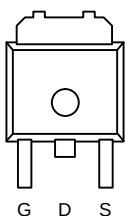
FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- PWM Optimized for High Efficiency

APPLICATIONS

- Synchronous Buck DC/DC Conversion
 - Desktop
 - Server

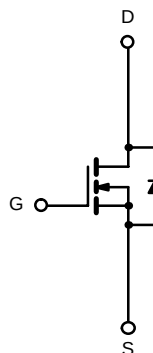
TO-252



Top View

Order Number:
SUD50N024-06P

Drain Connected to Tab



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Unit
Drain-Source Pulse Voltage		V _{DS(pulse)}	24 ^C	V
Drain-Source Voltage		V _{DS}	22	
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current ^a	T _C = 25°C	I _D	80 ^d	A
	T _C = 100°C		56 ^d	
Pulsed Drain Current		I _{DM}	100	
Continuous Source Current (Diode Conduction) ^a		I _S	26	
Avalanche Current, Single Pulse	L = 0.1 mH	I _{AS}	45	
Avalanche Energy, Single Pulse		E _{AS}	101	mJ
Maximum Power Dissipation	T _A = 25°C	P _D	6.8 ^a	W
	T _C = 25°C		65	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	18	22	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	1.9	2.3	

Notes

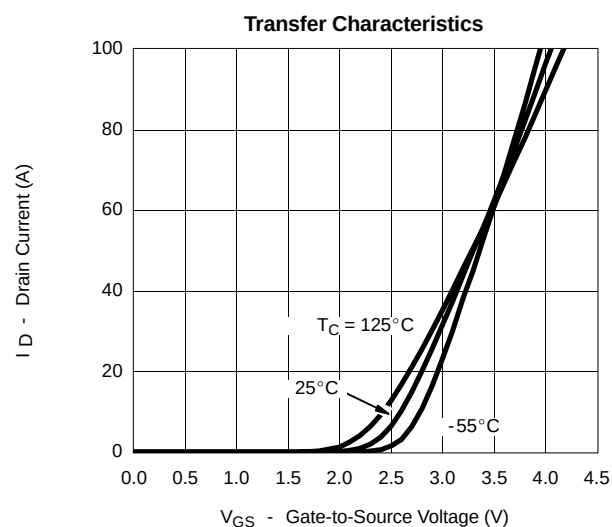
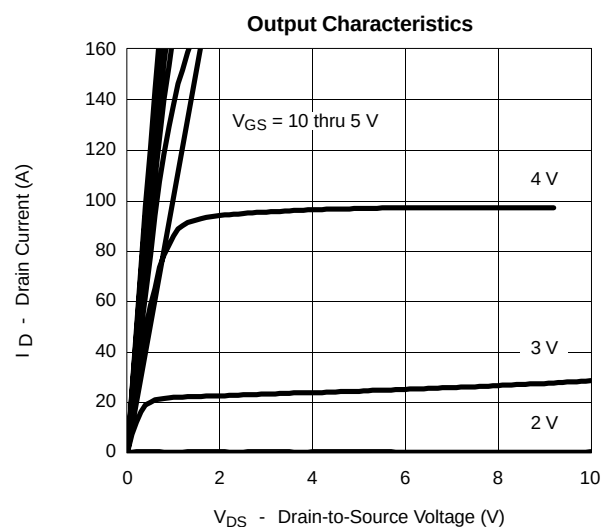
- a. Surface Mounted on FR4 Board, $t \leq 10$ sec.
 b. Limited by package
 c. Pulse condition: $T_A = 105^\circ\text{C}$, 50 ns, 300 kHz operation
 d. Calculation based on maximum allowable Junction Temperature. Package limitation current is 50 A.

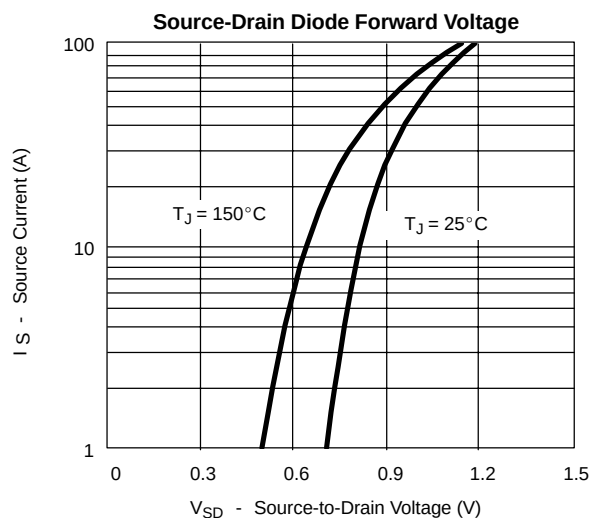
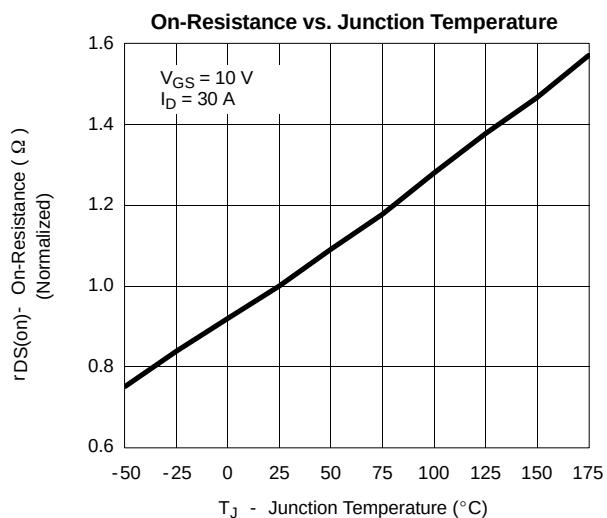
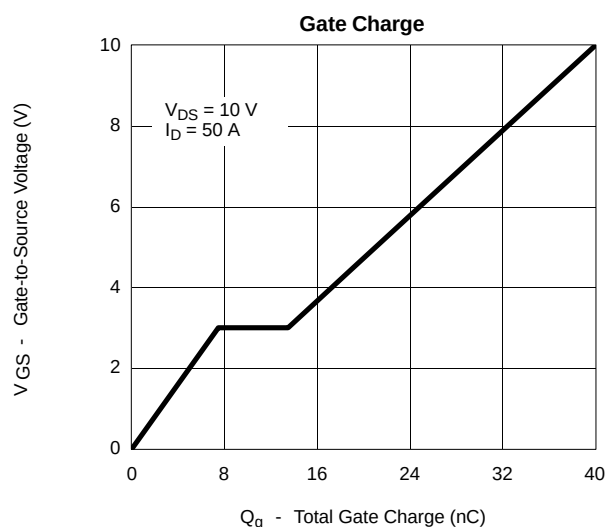
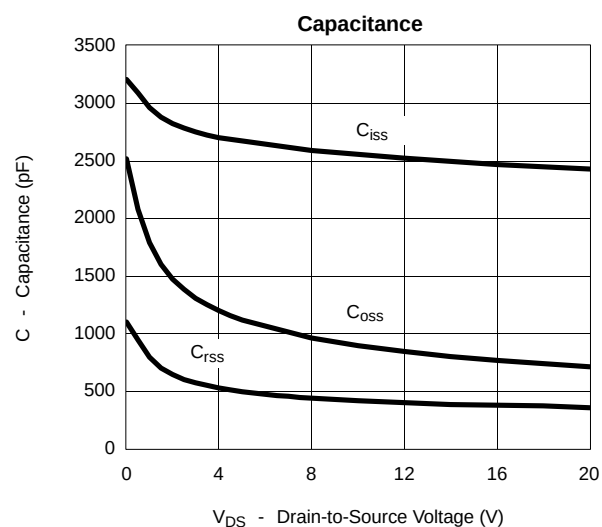
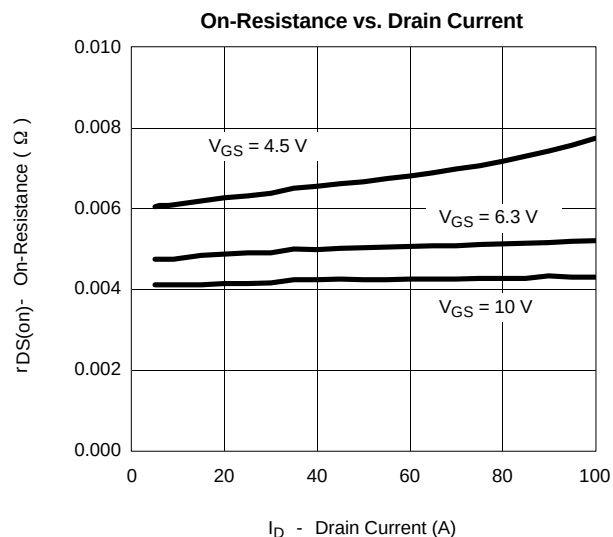
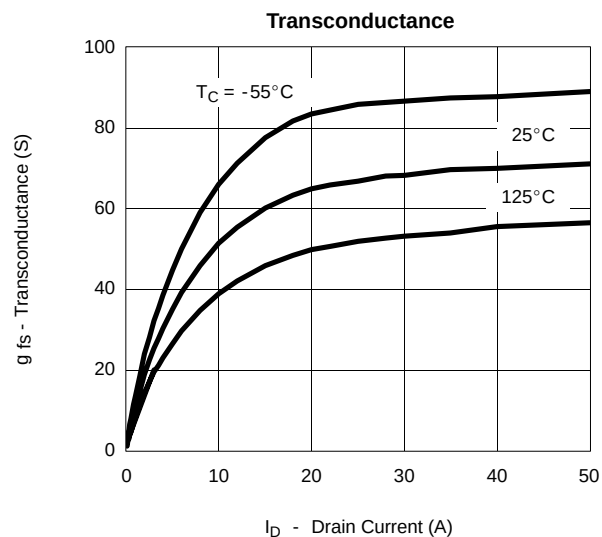
Vishay Siliconix**New Product**

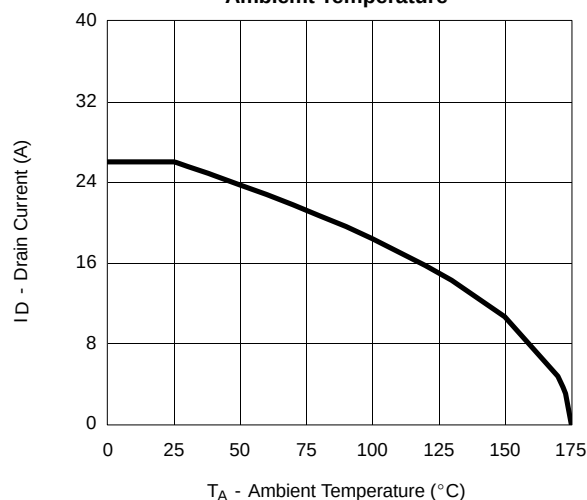
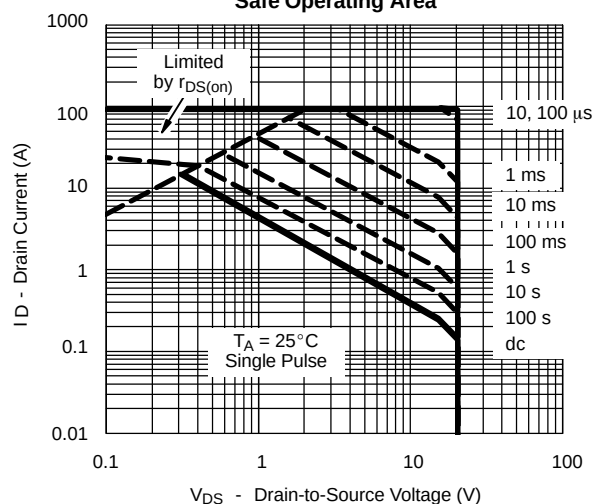
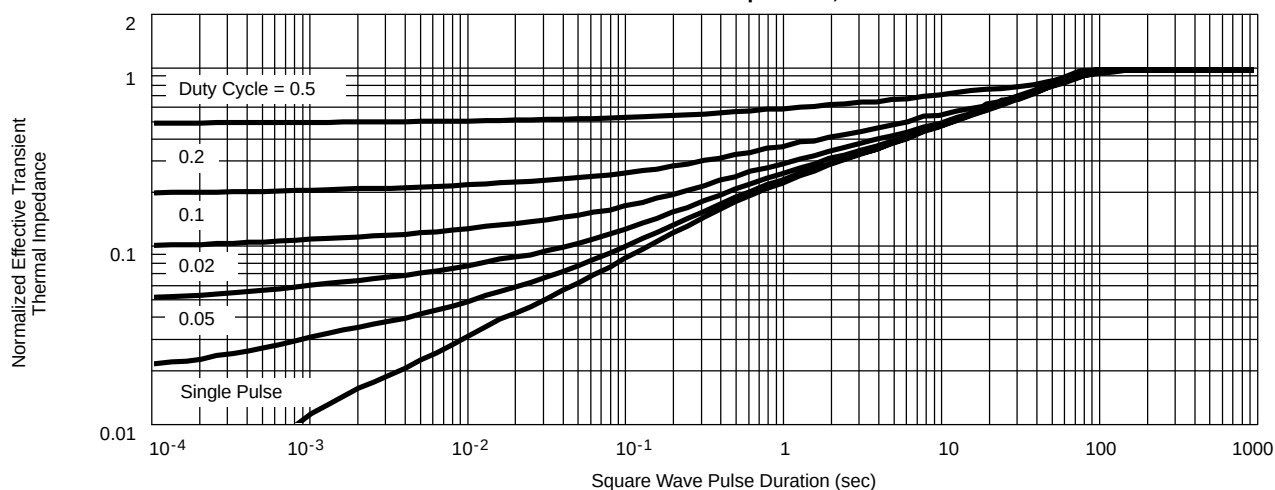
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	22			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.8		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V			1	μA
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 125 °C			50	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0046	0.006	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0084	
		V _{GS} = 4.5 V, I _D = 20 A		0.0073	0.0095	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	15			S
Dynamic ^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 10 V, f = 1 MHz		2550		pF
Output Capacitance	C _{oss}			900		
Reverse Transfer Capacitance	C _{rss}			415		
Gate Resistance	R _G			1.5		Ω
Total Gate Charge ^c	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 50 A		19	30	nC
Gate-Source Charge ^c	Q _{gs}			7.5		
Gate-Drain Charge ^c	Q _{gd}			6.0		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 10 V, R _L = 0.2 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _G = 2.5 Ω		11	20	ns
Rise Time ^c	t _r			10	15	
Turn-Off Delay Time ^c	t _{d(off)}			24	35	
Fall Time ^c	t _f			9	15	
Source-Drain Diode Ratings and Characteristic (T _C = 25 °C)						
Pulsed Current	I _{SM}				100	A
Diode Forward Voltage ^b	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		35	70	ns

Notes

- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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THERMAL RATINGS**Maximum Drain Current vs.
Ambient Temperature****Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**